

Description

This 30V,146A N-Channel MOSFET in a PDFN5*6 Plastic Package.

Features

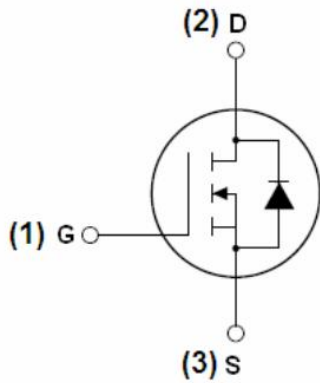
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- Halogen-Free Product

Applications

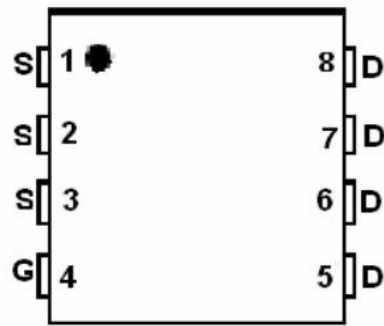
- Battery Management
- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

V_{DSS}	$R_{DS(on)}$ Typ	I_D
30V	1.5mΩ	146A

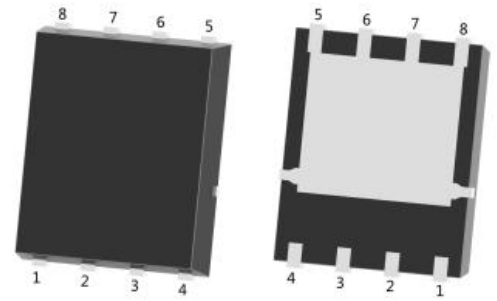
Equivalent Circuit & Pinning



Schematic diagram



Pin assignment



PDFN5X6-8L

Absolute Maximum Ratings(Ta=25°C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Drain Current - Continuous	I_D	146	A
Drain Current – Pulsed	I_{DM}	300	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	57	W
Single Pulse Avalanche Energy(L=0.5mH)	E_{AS}	315	mJ
Avalanche Current(L=0.5mH)	I_{AS}	30	A
Junction and Storage Temperature Range	T_j, T_{stg}	-55 to 150	°C
Thermal resistance, junction - ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	20
	Steady-State		50
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	2.2

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	30	35		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$			1.0	μA
Gate-Body leakage current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1	1.6	3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=24\text{A}$		1.5	1.8	m Ω
		$V_{GS}=4.5\text{V}, I_D=12\text{A}$		2.0	2.8	
Diode Forward Voltage	V_{SD}	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.68	1	V
Input Capacitance	C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1.0\text{MHz}$		8500		pF
Output Capacitance	C_{oss}			890		
Reverse Transfer Capacitance	C_{rss}			670		
Gate resistance	R_g	$V_{GS}=0\text{V}, f=1\text{MHz}, V_{DS}=0\text{V}$		1.8		Ω
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10\text{V}, I_D=20\text{A}, V_{DS}=15\text{V}$		60		nC
Total Gate Charge	$Q_{g(4.5V)}$			28		
Gate Source Charge	Q_{gs}			12		
Gate Drain Charge	Q_{gd}			9.5		

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=0.75\ \Omega$ $R_{GEN}=3\ \Omega$		12.5		ns
Turn-On Rise Time	t_r			6.0		
Turn-Off Delay Time	$t_{d(off)}$			47		
Turn-Off Fall Time	t_f			10.5		

Electrical Characteristic Curve

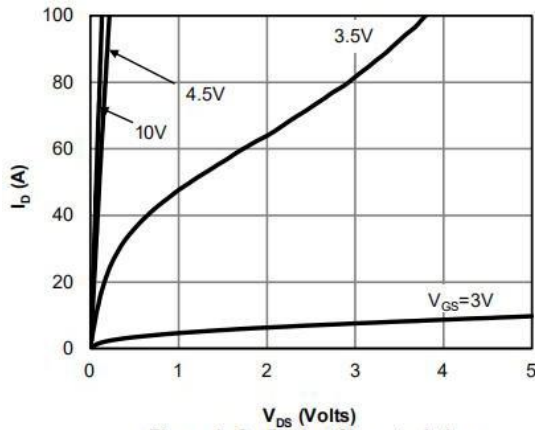


Figure 1: On-Region Characteristics

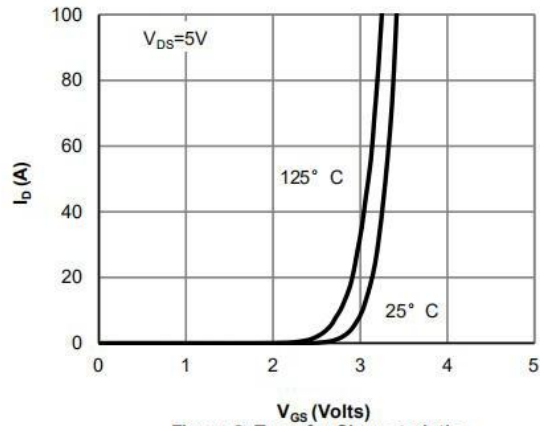


Figure 2: Transfer Characteristics

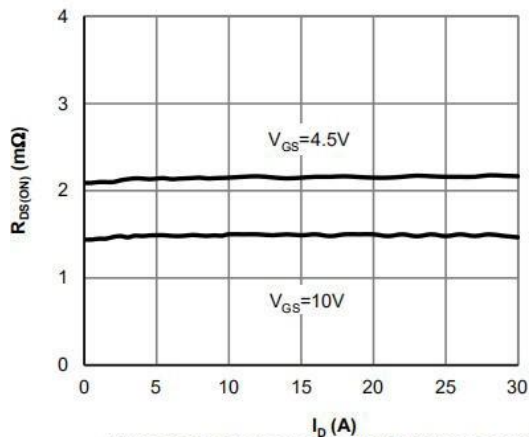


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

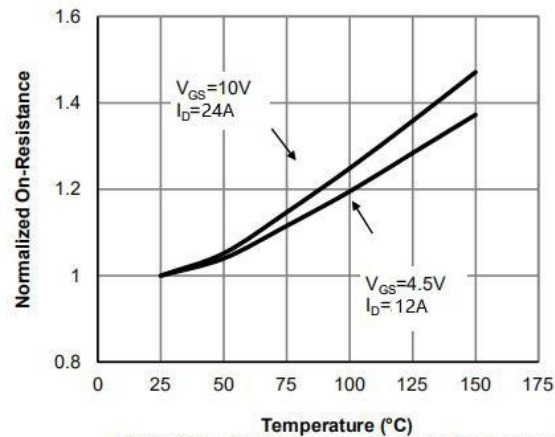


Figure 4: On-Resistance vs. Junction Temperature

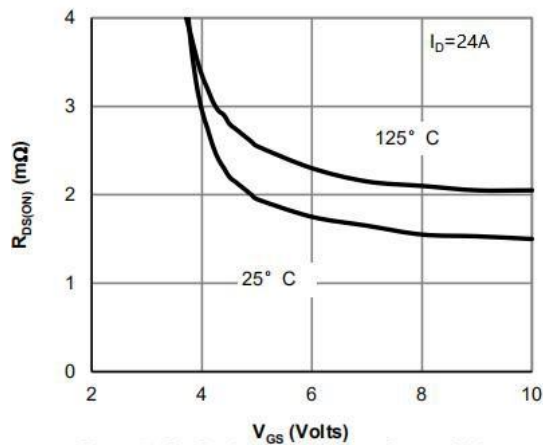


Figure 5: On-Resistance vs. Gate-Source Voltage

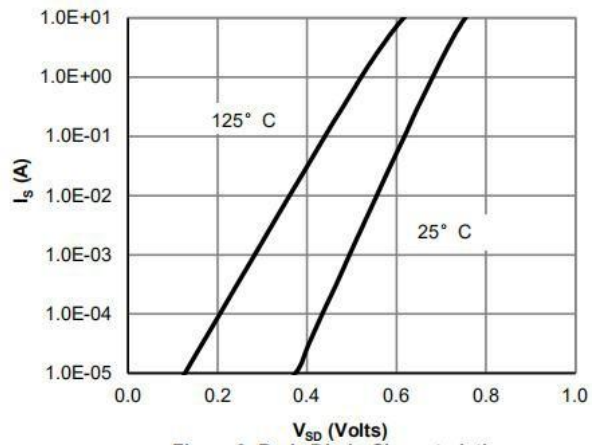


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

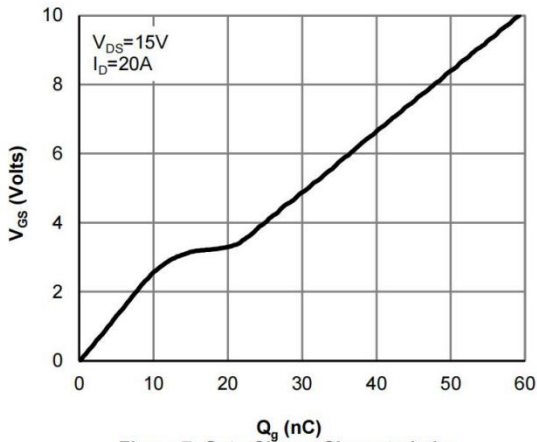


Figure 7: Gate-Charge Characteristics

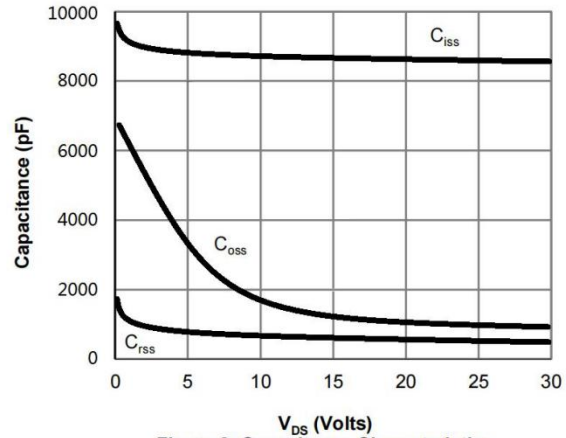


Figure 8: Capacitance Characteristics

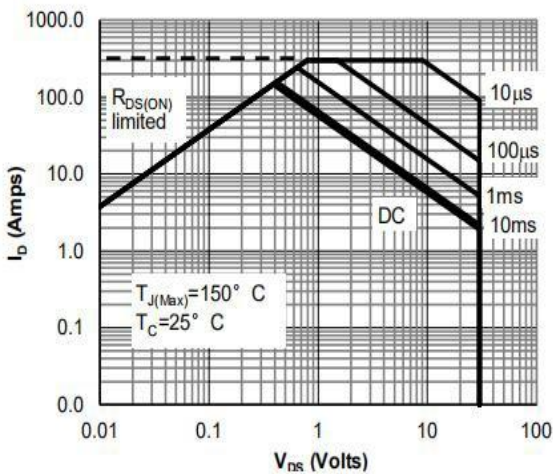


Figure 9: Maximum Forward Biased Safe Operating Area

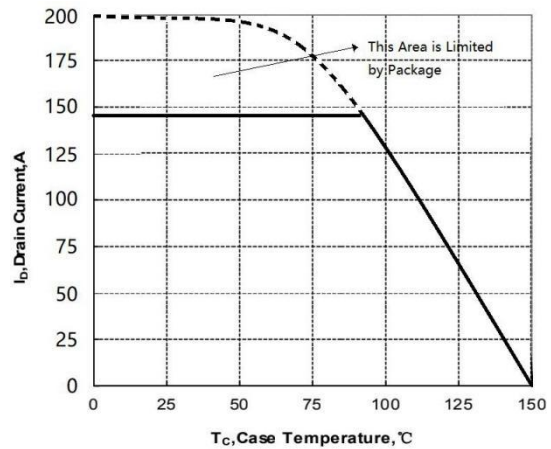


Figure 10: Maximum Continuous Drain Current vs Case Temperature

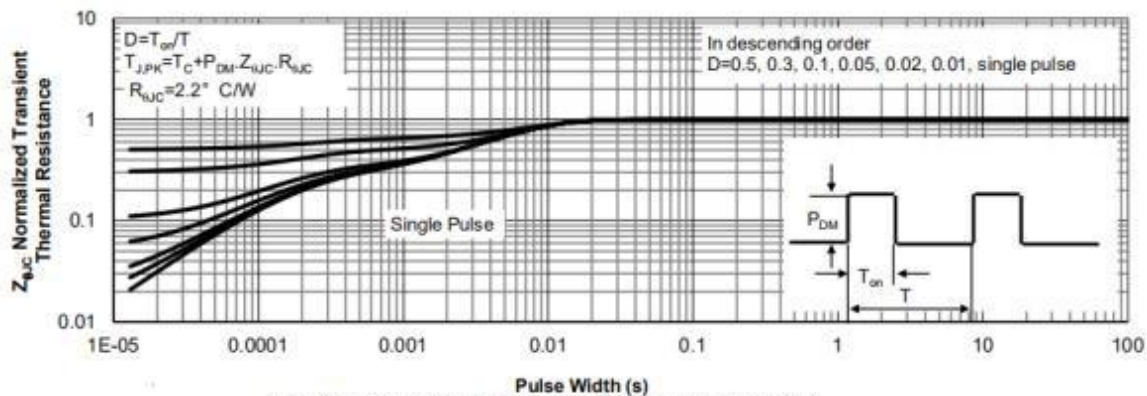
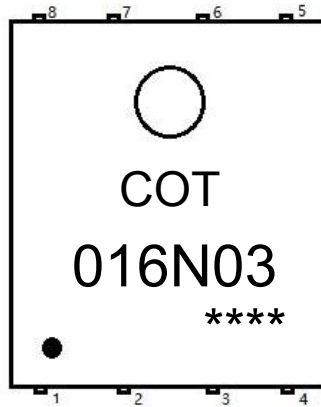


Figure 11: Normalized Maximum Transient Thermal Impedance

Marking Instructions



Note:

COT: Company Logo

016N03: Product Type.

****: Lot No. Code, code change with Lot No.

Packaging SPEC.

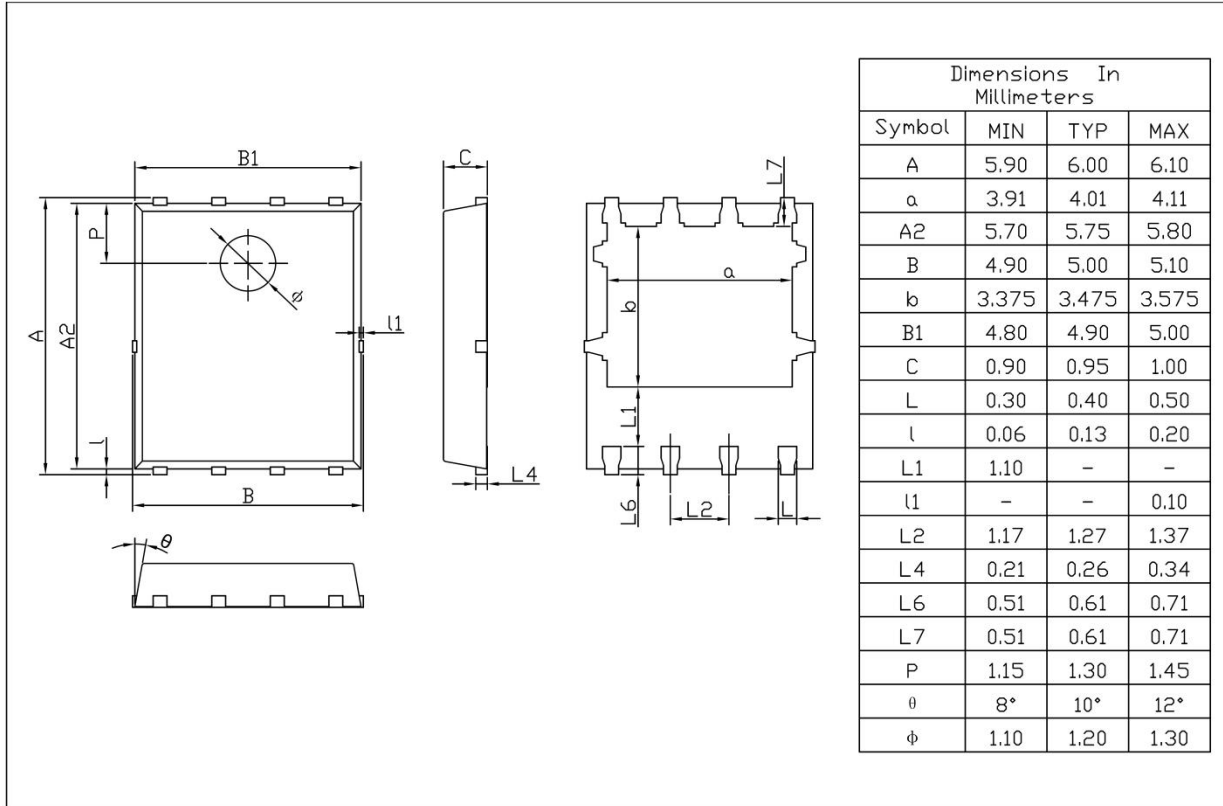
REEL INFORMATION

Package Type	Units					Dimension (unit: mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
PDFN5*6	5000	2	10000	6	60000	13" × 12	360 × 360 × 50	380 × 335 × 366

Package Outline Dimensions

PDFN5 X6

Unit:mm



Rev.01 202209